

LS133

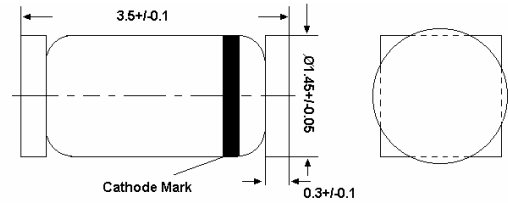
SILICON EPITAXIAL PLANAR DIODE

High speed switching diode

Features

- Glass sealed envelope
- High speed
- High reliability

LS-34



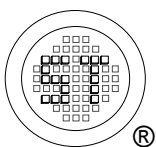
QuadroMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Mean Rectifying Current	I_o	130	mA
Peak Forward Current	I_{FM}	400	mA
Surge Current (1s)	I_{surge}	600	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_s	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 80\text{ V}$	I_R	0.5	μA
Capacitance Between Terminals at $V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_T	2	pF
Reverse Recovery Time at $V_R = 6\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 50\ \Omega$	t_{rr}	4	ns



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

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